

Analytical determination of the reach-through breakdown voltage of bipolar transistors, asymmetric thyristors and Punch Through-IGBTs

Miron J. Cristea

'POLITEHNICA University of Bucharest', Bucharest, Romania
E-mail: mcris@lydo.org Tel: 40-214-024-915 Fax: 40-214-300-555

Introduction

In this work, an analytical formula that gives the reach-through breakdown voltage of bipolar transistors, asymmetric thyristors, Punch Through-IGBTs and other devices with similar structure is deduced for the first time.

Breakdown voltage determination

In an earlier work [1] we have established the formula:

$$\int_{SCR} \frac{x}{\varepsilon} \rho(x) dx = V_{bi} - V_F = V_{bi} + V_R \quad (1)$$

where ε is the dielectric permittivity of semiconductor, $\rho(x)$ - the density of electric charge in the space charge region of the junction (SCR), V_{bi} is the built-in potential of the junction, V_F - the external forward bias applied on the junction and V_R - the reverse voltage applied to the junction - if it is reverse biased.

This formula will be used to determine the breakdown voltage by the reach-through of the base of a bipolar transistor (Fig.1). The semiconductor is supposed to be homogenous (e.g. silicon).

$$-\frac{q}{\varepsilon} \int_{-W_p}^0 x \left[N_0 \exp\left(-\frac{x^2}{L_d^2}\right) - N_B \right] dx + \frac{q}{\varepsilon} \int_0^{W_n} x N_B dx = V_{biC} + V_R \quad (2)$$

In equation (2) q is the elementary electric charge, N_0 is the surface concentration of the base diffusion, N_B is the constant concentration of the n^- central layer, L_d the technological diffusion length of the base doping and V_{biC} is the built-in potential of the collector junction. W_n is the extension of the SCR in the lightly doped n^- layer, equal with the physical n^- layer width because of the n field stopper layer and W_p is the extension of the depletion region in the base (Fig.1):

$$\begin{aligned} & \frac{q}{\epsilon} \left[\frac{L_d^2}{2} N_0 \exp\left(-\frac{x^2}{L_d^2}\right) + \frac{x^2}{2} N_B \right] \Big|_{-W_p}^0 + \frac{q}{2\epsilon} N_B x^2 \Big|_0^{W_n} = \\ & = \frac{qL_d^2}{2\epsilon} N_0 \left[1 - \exp\left(-\frac{W_p^2}{L_d^2}\right) \right] - \frac{q}{2\epsilon} N_B W_p^2 + \frac{q}{2\epsilon} N_B W_n^2 = \\ & = V_R + V_{biC} \end{aligned} \quad (3)$$

At reach-through:

$$\begin{aligned} & \frac{qL_d^2}{2\epsilon} N_0 \left[1 - \exp\left(-\frac{W_{pRT}^2}{L_d^2}\right) \right] - \frac{q}{2\epsilon} N_B W_{pRT}^2 + \frac{q}{2\epsilon} N_B W_n^2 = \\ & = V_{BRT} + V_{biC} \end{aligned} \quad (4)$$

where V_{BRT} is the reach-through breakdown voltage and W_{pRT} is the depletion region in the base at reach-through equal to the physical width of the base - W_{B0} , less the space charge region width of the p-side of the emitter junction, W_{SEP} . (We suppose that the transistor does not break before reach-through, by attaining the critical field at the collector junction.)

$$W_{pRT} = W_{B0} - W_{SEP} \quad (5)$$

with W_{SEP} - the depletion region extended in the base from the emitter [2]:

$$W_{SEP} = L_d \left\{ \sqrt{-\ln \left[e^{-\frac{x_{je}^2}{L_d^2}} - \frac{2\epsilon}{qN_0L_d^2} (V_{biE} - V_{BE}) \right]} \right\} - x_{jE} \quad (6)$$

where x_{jE} is the emitter-base metallurgical junction depth (Fig.1.), V_{biE} is the built-in potential of the emitter junction and V_{BE} - the external bias applied on the emitter-base junction.

The resulting formula of the reach-through breakdown voltage is:

$$V_{BRT} = \frac{qN_D}{2\epsilon} \cdot (W_n^2 - W_{pRT}^2) + \frac{qL_d^2N_0}{2\epsilon} \left(1 - e^{-\frac{W_{pRT}^2}{L_p^2}} \right) - V_{biC} \quad (7)$$

In the case of asymmetric thyristors and the PT-IGBTs (Punch Through IGBTs), the value of the reach-through voltage of the p-base is the same. The structural difference is the presence of a p^+ layer at the exterior (Fig.1.) that does not influence the reach-through of the base at the $p-n^-$ junction.

Acknowledgement

The author thanks Miss Rocsana Ionescu for carefully preparation of the drawing.

Conclusion

In this work, an analytical formula was calculated for the reach-through breakdown voltage of semiconductor devices like bipolar transistors, asymmetric thyristors, Punch Through IGBTs and other devices with similar structure.

References

- [1] Miron J. Cristea, **Integral equation for electrically charged space regions - theory and applications**, arXiv:math-ph/0608068, 31 Aug 2006.

[2] Miron J. Cristea, **First time calculation of the depletion region width and barrier capacitance of practical diffused semiconductor junctions**, arXiv:math-ph/0609004, 1 Sep 2006.

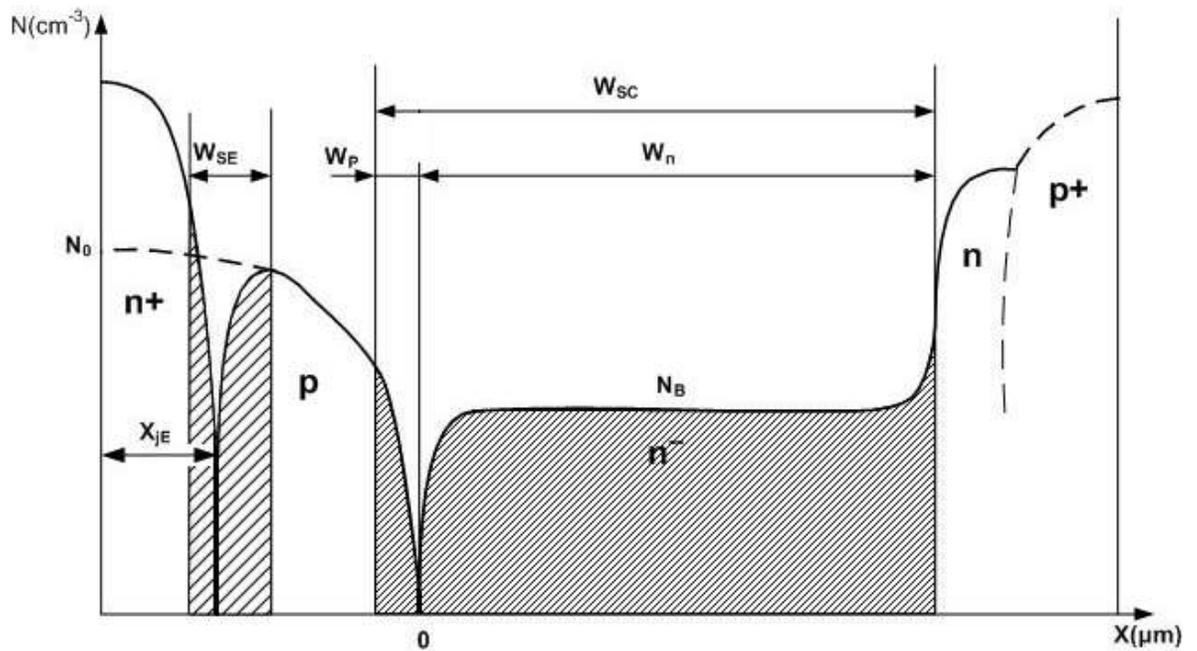


Figure 1. The doping profile of a bipolar transistor - without the p^+ layer, respectively of an asymmetric thyristor/PT-IGBT - with the p^+ layer. The base profile is Gaussian.